



FDP8443

N-Channel PowerTrench® MOSFET

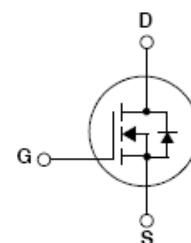
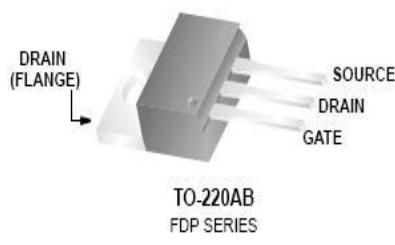
40V, 80A, 3.5mΩ

Features

- Typ $r_{DS(on)}$ = 2.7mΩ at $V_{GS} = 10V$, $I_D = 80A$
- Typ $Q_g(10) = 142nC$ at $V_{GS} = 10V$
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- Qualified to AEC Q101
- RoHS Compliant

Applications

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Electronic Steering
- Integrated Starter / Alternator
- Distributed Power Architecture and VRMs
- Primary Switch for 12V Systems



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	40	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current Continuous ($T_C < 144^\circ\text{C}$, $V_{GS} = 10\text{V}$)	80	A
	Continuous ($T_{amb} = 25^\circ\text{C}$, $V_{GS} = 10\text{V}$, with $R_{0JA} = 62^\circ\text{C/W}$)	20	
	Pulsed	See Figure 4	
E_{AS}	Single Pulse Avalanche Energy (Note 1)	531	mJ
P_D	Power Dissipation	188	W
	Derate above 25°C	1.25	$\text{W}/^\circ\text{C}$
T_J , T_{STG}	Operating and Storage Temperature	-55 to +175	$^\circ\text{C}$

Thermal Characteristics

R_{0JC}	Thermal Resistance Junction to Case	0.8	$^\circ\text{C/W}$
R_{0JA}	Thermal Resistance Junction to Ambient (Note 2)	62	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP8443	FDP8443	TO-220AB	Tube	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

B_{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 32\text{V}$,	-	-	1	μA
		$V_{GS} = 0\text{V}$ $T_C = 150^\circ\text{C}$	-	-	250	
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2	2.8	4	V
$r_{DS(on)}$	Drain to Source On Resistance	$I_D = 80\text{A}$, $V_{GS} = 10\text{V}$	-	2.7	3.5	$\text{m}\Omega$
		$I_D = 80\text{A}$, $V_{GS} = 10\text{V}$, $T_J = 175^\circ\text{C}$	-	4.7	6.1	

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	-	9310	-	pF	
C_{oss}	Output Capacitance		-	800	-	pF	
C_{rss}	Reverse Transfer Capacitance		-	510	-	pF	
R_G	Gate Resistance	$V_{GS} = 0.5\text{V}$, $f = 1\text{MHz}$	-	0.9	-	Ω	
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V	-	142	185	nC	
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0$ to 2V	$V_{DD} = 20\text{V}$ $I_D = 35\text{A}$ $I_g = 1\text{mA}$	-	17.5	23	nC
Q_{gs}	Gate to Source Gate Charge	-		36	-	nC	
Q_{gs2}	Gate Charge Threshold to Plateau	-		18.8	-	nC	
Q_{gd}	Gate to Drain "Miller" Charge	-		32	-	nC	

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Switching Characteristics ($V_{GS} = 10\text{V}$)

t_{on}	Turn-On Time	$V_{DD} = 20\text{V}, I_D = 35\text{A}$ $V_{GS} = 10\text{V}, R_{GS} = 2\Omega$	-	-	58	ns
$t_{d(on)}$	Turn-On Delay Time		-	18.4	-	ns
t_r	Rise Time		-	17.9	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	55	-	ns
t_f	Fall Time		-	13.5	-	ns
t_{off}	Turn-Off Time		-	-	109	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 35\text{A}$	-	0.8	1.25	V
		$I_{SD} = 15\text{A}$	-	0.8	1.0	
t_{rr}	Reverse Recovery Time	$I_{SD} = 35\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	42	55	ns
			-	48	62	

Notes:

- 1: Starting $T_J = 25^\circ\text{C}$, $L = 0.26\text{mH}$, $I_{AS} = 64\text{A}$.
2: Pulse width = 100s.

Typical Characteristics

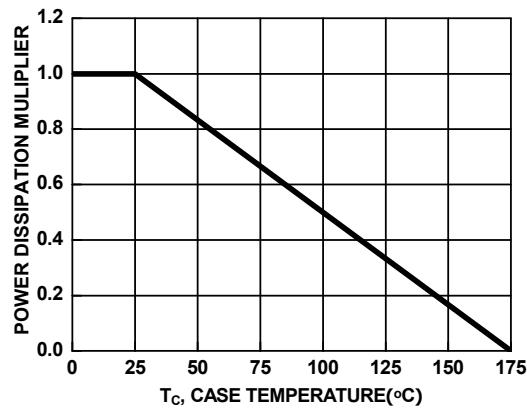


Figure 1. Normalized Power Dissipation vs Case Temperature

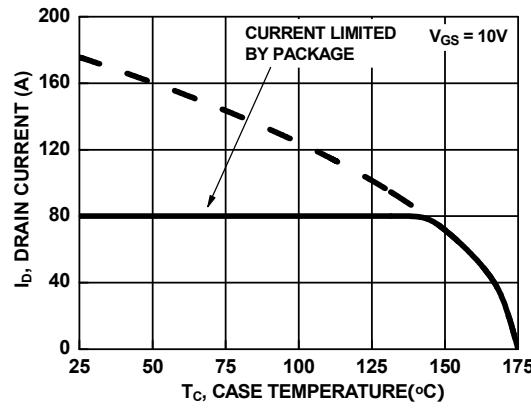


Figure 2. Maximum Continuous Drain Current vs Case Temperature

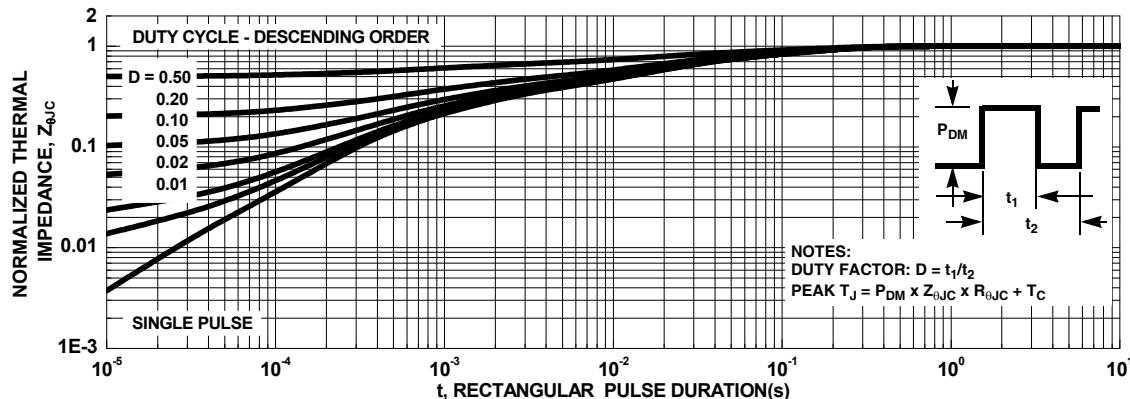


Figure 3. Normalized Maximum Transient Thermal Impedance

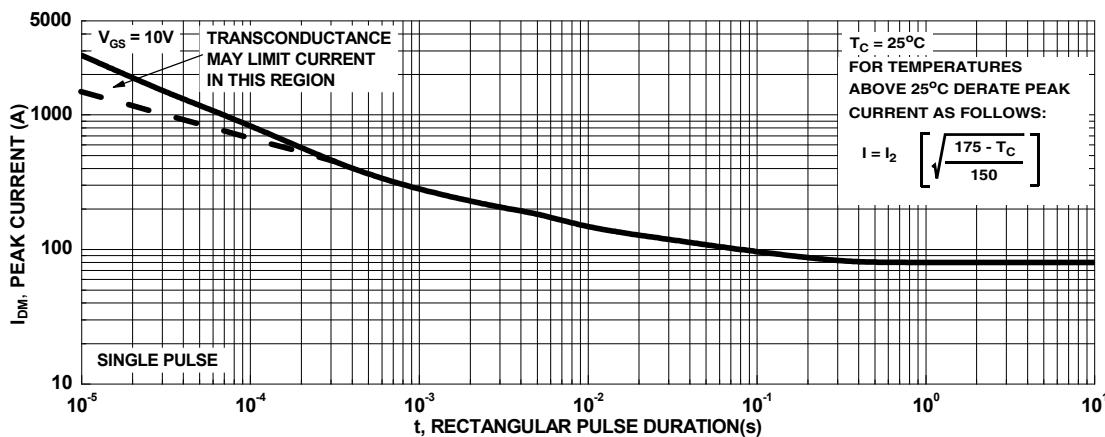


Figure 4. Peak Current Capability